



STPS30L30CT/CG/CR

LOW DROP POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

$I_{F(AV)}$	2 x 15 A
V_{RRM}	30 V
$T_j (max)$	150 °C
$V_F (max)$	0.37 V

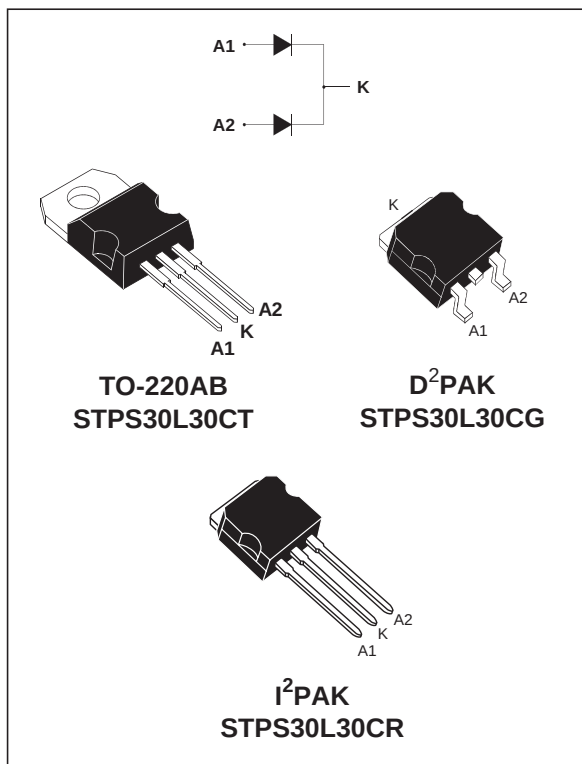
FEATURES AND BENEFITS

- VERY SMALL CONDUCTION LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- EXTREMELY FAST SWITCHING
- LOW FORWARD VOLTAGE DROP
- LOW THERMAL RESISTANCE
- AVALANCHE CAPABILITY SPECIFIED

DESCRIPTION

Dual center tap Schottky rectifiers suited for Switch Mode Power Supply and high frequency DC to DC converters.

Packaged in TO-220AB, D²PAK and I²PAK, these devices are intended for use in low voltage, high frequency inverters, free-wheeling and polarity protection applications.



ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter			Value	Unit
V _{RRM}	Repetitive peak reverse voltage			30	V
I _{F(RMS)}	RMS forward current			30	A
I _{F(AV)}	Average forward current	T _c = 140°C δ = 0.5	Per diode Per device	15 30	A
I _{FSM}	Surge non repetitive forward current	t _p = 10 ms Sinusoidal		220	A
I _{RRM}	Peak repetitive reverse current	t _p = 2 μs F = 1kHz square		1	A
I _{RSM}	Non repetitive peak reverse current	t _p = 100μs square		3	A
P _{ARM}	Repetitive peak avalanche power	t _p = 1μs T _j = 25°C		5300	W
T _{stg}	Storage temperature range			- 65 to + 150	°C
T _j	Maximum operating junction temperature *			150	°C
dV/dt	Critical rate of rise reverse voltage			10000	V/μs

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THERMAL RESISTANCE

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case	Per diode Total	1.5 0.8	°C/W
$R_{th(c)}$		Coupling	0.1	°C/W

When the diodes 1 and 2 are used simultaneously :

$$\Delta T_j(\text{diode } 1) = P(\text{diode } 1) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode } 2) \times R_{th(c)}$$

STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit
I_R^*	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$			1.5	mA
		$T_j = 125^\circ\text{C}$			170	350	mA
V_F^*	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 15\text{ A}$			0.46	V
		$T_j = 125^\circ\text{C}$	$I_F = 15\text{ A}$		0.33	0.37	
		$T_j = 25^\circ\text{C}$	$I_F = 30\text{ A}$			0.57	
		$T_j = 125^\circ\text{C}$	$I_F = 30\text{ A}$		0.43	0.5	

Pulse test : * $t_p = 380\text{ }\mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation :

$$P = 0.24 \times I_{F(AV)} + 0.009 I_{F(RMS)}^2$$

Fig. 1: Average forward power dissipation versus average forward current (per diode).

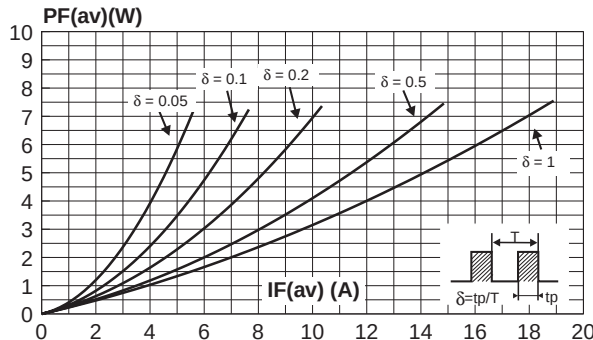


Fig. 3: Normalized avalanche power derating versus pulse duration.

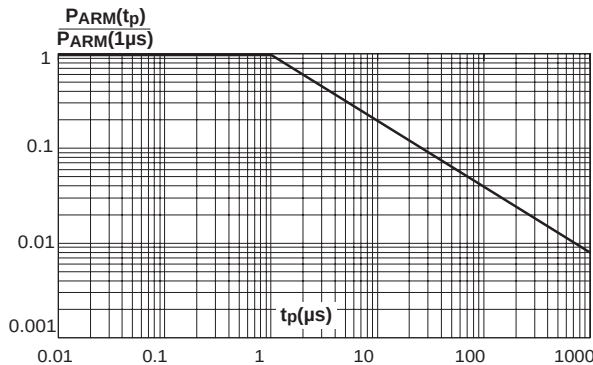


Fig. 2: Average current versus ambient temperature ($\delta=0.5$) (per diode).

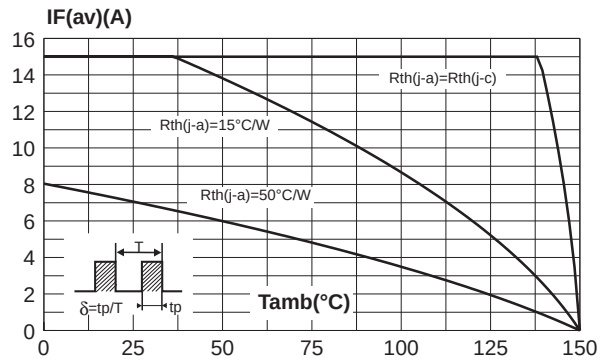


Fig. 4: Normalized avalanche power derating versus junction temperature.

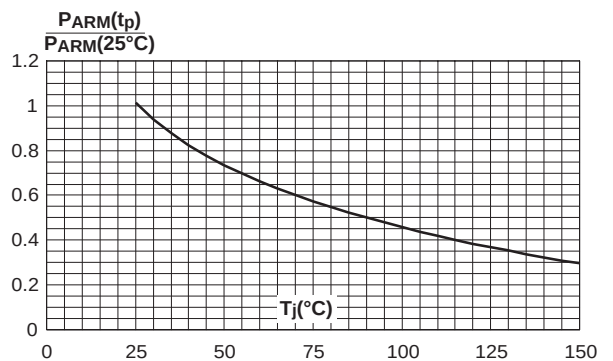


Fig. 4: Non repetitive surge peak forward current versus overload duration (maximum values) (per diode).

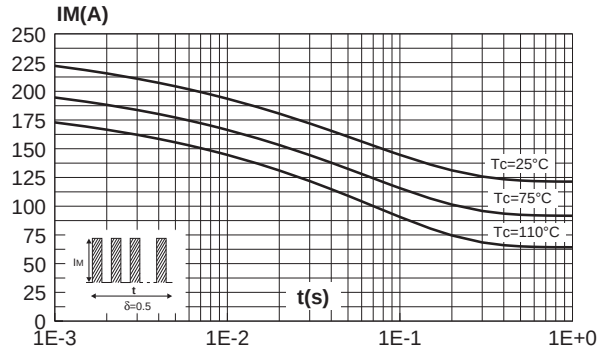


Fig. 5: Relative variation of thermal transient impedance junction to case versus pulse duration.

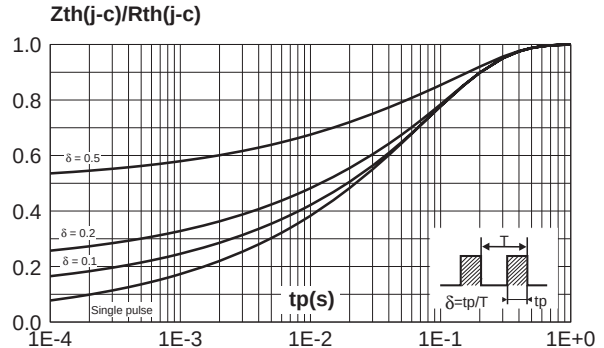


Fig. 6: Reverse leakage current versus reverse voltage applied (typical values) (per diode).

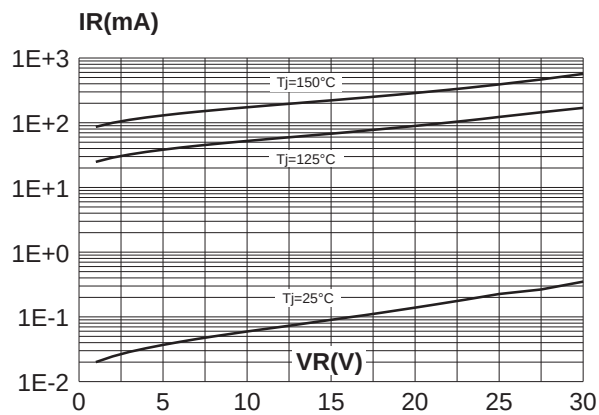


Fig. 7: Junction capacitance versus reverse voltage applied (typical values) (per diode).

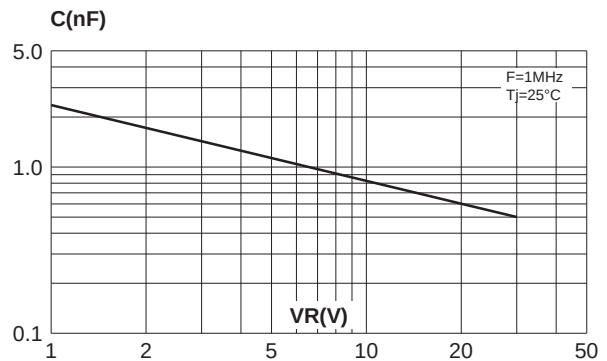


Fig. 8: Forward voltage drop versus forward current (maximum values - per diode).

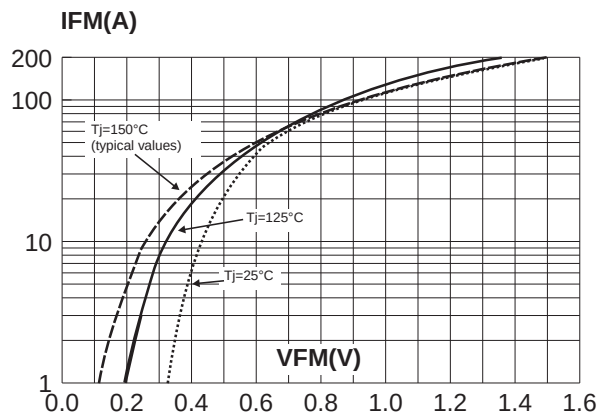
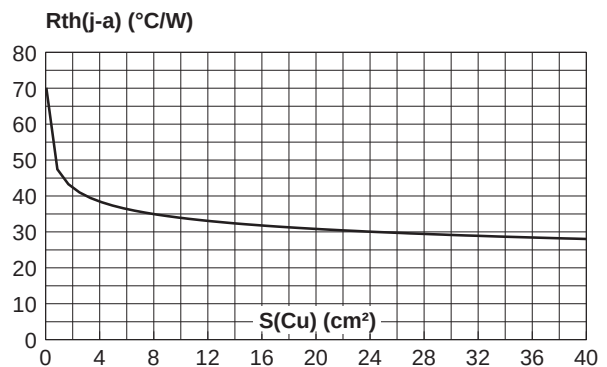
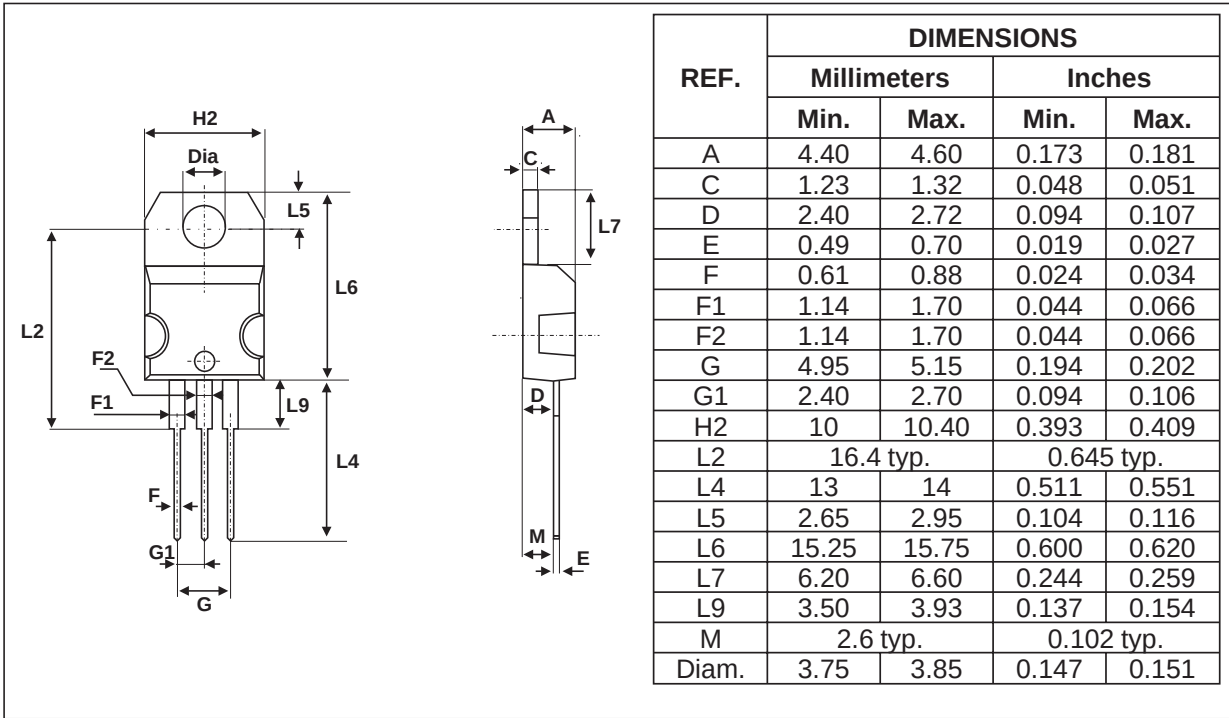


Fig. 9: Thermal resistance junction to ambient versus copper surface under tab (epoxy printed circuit board FR4, $e(\text{Cu}) = 35\ \mu\text{m}$) (STPS30L30CG).



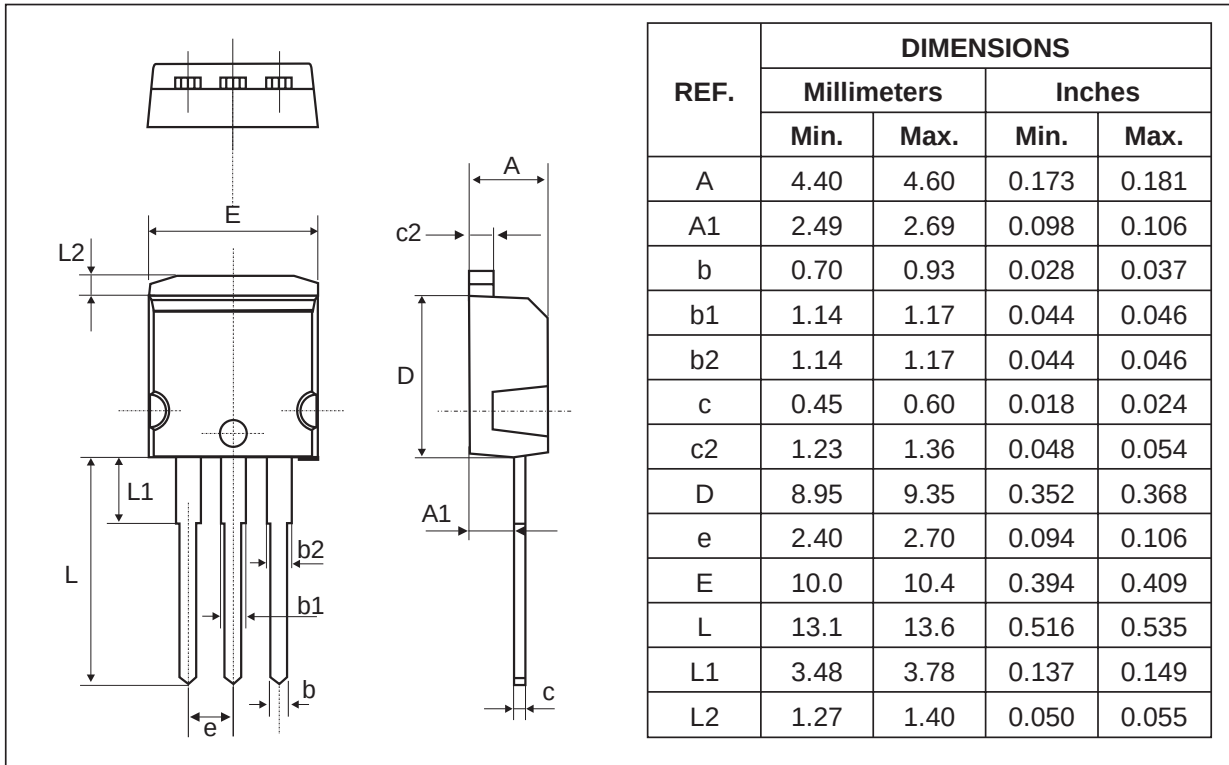
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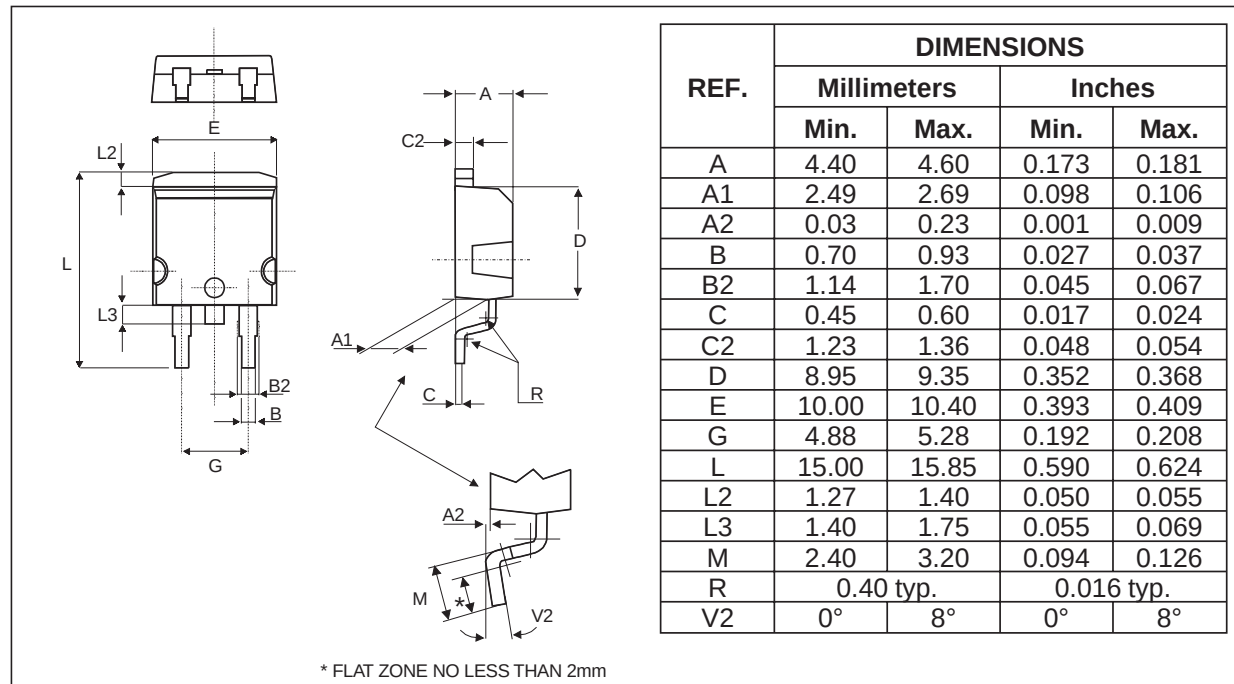
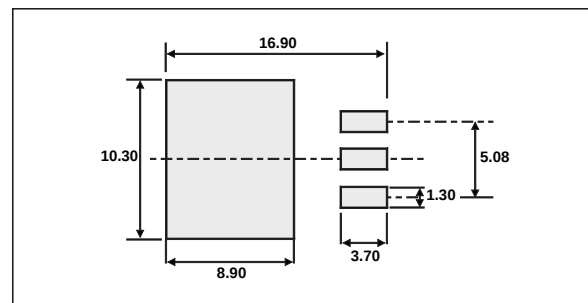
PACKAGE MECHANICAL DATA
TO-220AB



- Cooling method: C
- Recommended torque value: 0.55 m.N
- Maximum torque value: 0.70 m.N

PACKAGE MECHANICAL DATA
I²PAK



PACKAGE MECHANICAL DATA
D²PAK

FOOT PRINT (in millimeters)


Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS30L30CT	STPS30L30CT	TO-220AB	2g	50	Tube
STPS30L30CG	STPS30L30CG	D ² PAK	1.8g	50	Tube
STPS30L30CG-TR	STPS30L30CG	D ² PAK	1.8g	1000	Tape & reel
STPS30L30CR	STPS30L30CR	I ² PAK	1.49g	50	Tube

- Epoxy meets UL94,V0

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